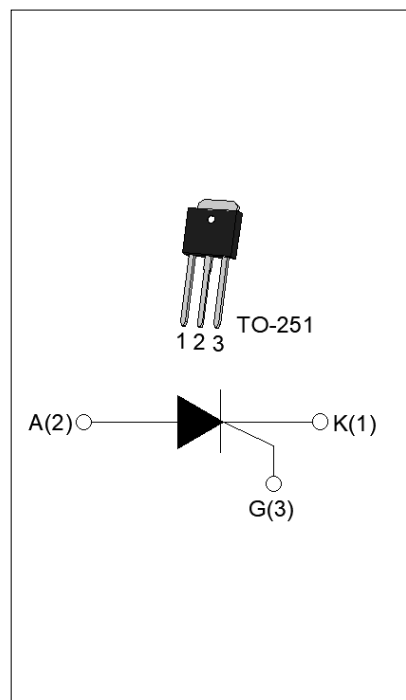




With high ability to withstand the shock loading of large current, JCT810H of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-251 is RoHS compliant.

Symbol	Value	Unit
$I_{T(RMS)}$	10	A
V_{DRM}/V_{RRM}	800	V
I_{GT}	10	mA



Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
Average on-state current ($T_c = 63^\circ\text{C}$)	$I_{T(AV)}$	6.5	A
RMS on-state current ($T_c = 63^\circ\text{C}$)	$I_{T(RMS)}$	10	A
Non repetitive surge peak on-state current ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I_{TSM}	110	A
Non repetitive surge peak on-state current ($t_p=8.3\text{ms}, T_j=25^\circ\text{C}$)		120	
I^2t value for fusing ($t_p=10\text{ms}, T_j=25^\circ\text{C}$)	I^2t	61	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}, f=100\text{Hz}, T_j=125^\circ\text{C}$)	di/dt	100	A/s
Peak gate current ($t_p=20\text{ }\mu\text{s}, T_j=125^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

($T_j=25$ unless otherwise specified)

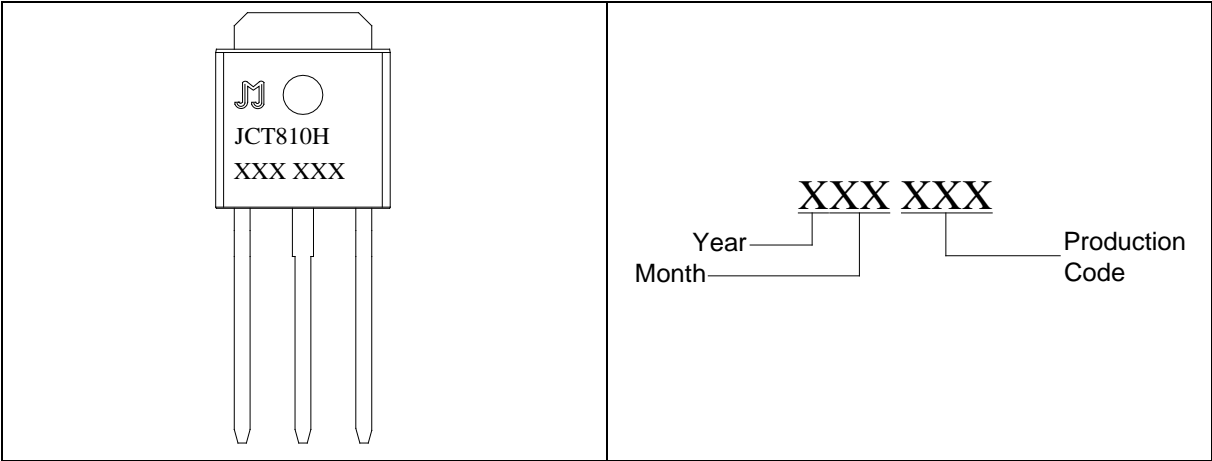
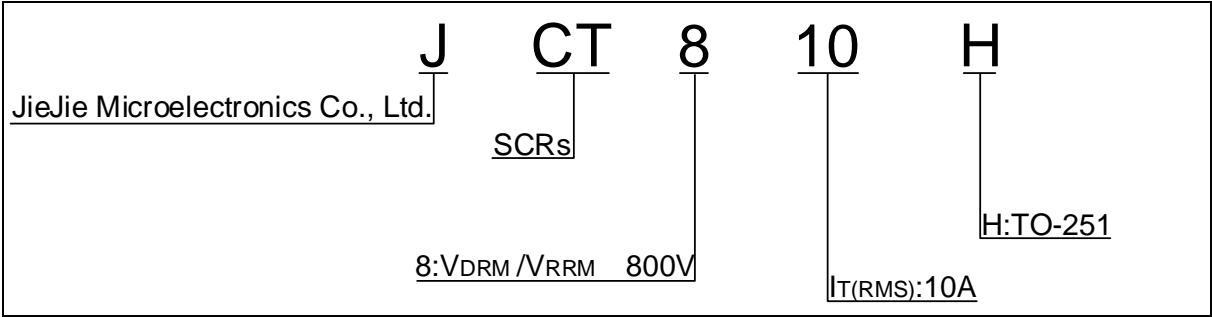


FIG.1 Maximum power dissipation versus RMS on-state current

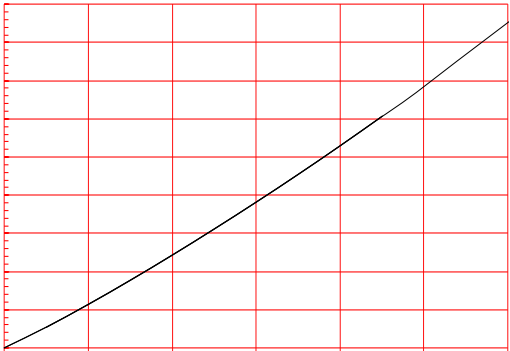


FIG.2: RMS on-state current versus case temperature

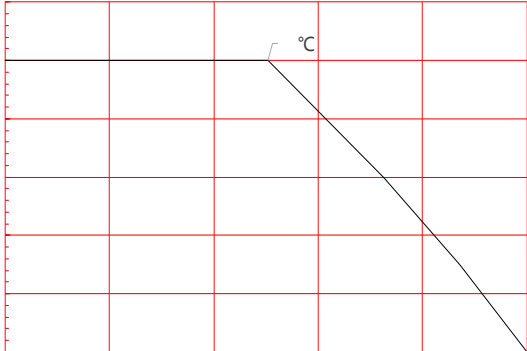
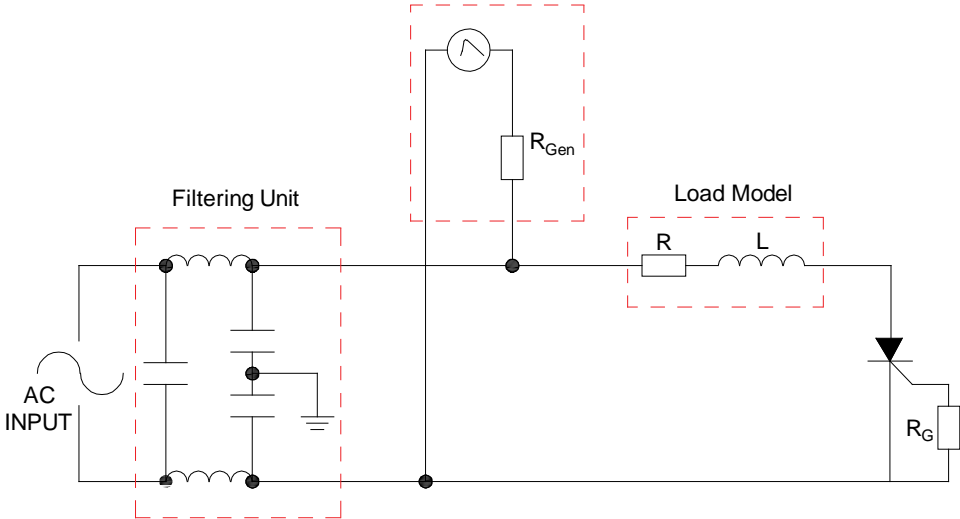
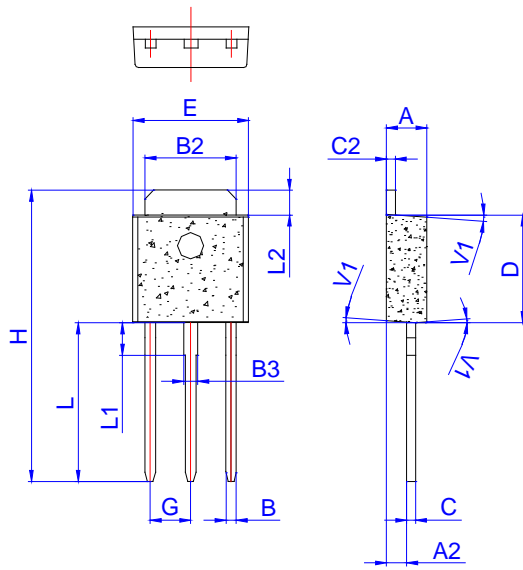


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

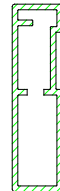
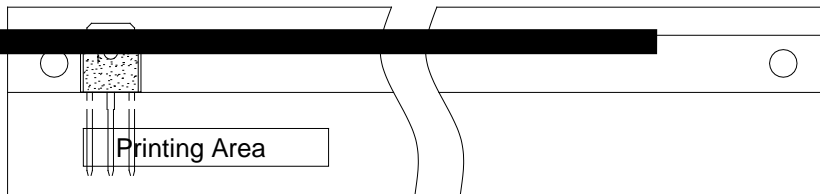
IEC61000-4-5 Standards
Surge Generator




Order code



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1		4°			4°	



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